查询IRK.F82.. SERIES供应商

Bulletin I27103 rev. A 09/97

International
IOR Rectifier

IRK.F82.. SERIES

FAST THYRISTOR/ DIODE and THYRISTOR/ THYRISTOR

INT-A-pak™ Power Modules

81 A

Features

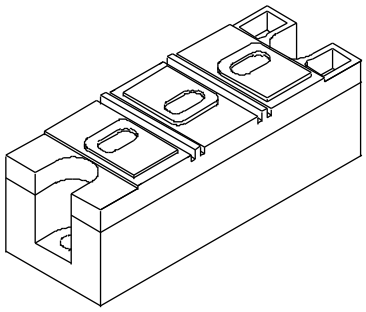
- Fast turn-off thyristor
- Fast recovery diode
- High surge capability
- Electrically isolated baseplate
- 3000 V_{RMS} isolating voltage
- Industrial standard package
- UL E78996 approved

Description

These series of INT-A-pak modules are intended for applications such as self-commutated inverters, DC choppers, electronic welders, induction heating and others where fast switching characteristics are required.

Major Ratings and Characteristics

Parameters		IRK.F82..	Units
$I_{T(AV)}$		81	A
	@ T_C	90	°C
$I_{T(RMS)}$		180	A
I_{TSM}	@ 50Hz	2200	A
	@ 60Hz	2300	A
I^2t	@ 50Hz	24.2	KA^2s
	@ 60Hz	22.1	KA^2s
$I^2\sqrt{t}$		242	$KA^2\sqrt{s}$
t_q	range	10 and 15	µs
t_{rr}		2	µs
V_{DRM}/V_{RRM}		up to 800	V
T_J	range	-40 to 125	°C

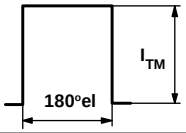
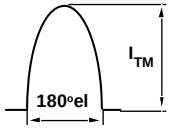
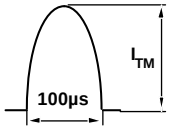


ELECTRICAL SPECIFICATIONS

Voltage Ratings

Type number	Voltage Code	V_{RRM}/V_{DRM}, maximum repetitive peak reverse voltage V	V_{RSM}, maximum non-repetitive peak rev. voltage V	I_{RRM}/I_{DRM} max. @ T_J = 125°C mA
IRK.F82..	04	400	400	30
	08	800	800	

Current Carrying Capacity

Frequency f							Units
50Hz	160	265	250	400	2240	3100	A
400Hz	200	320	290	475	1070	1550	A
2500Hz	150	240	260	400	370	550	A
5000Hz	135	215	235	355	235	355	A
10000Hz	90	160	190	275	-	-	A
Recovery voltage Vr	50	50	50	50	50	50	V
Voltage before turn-on Vd	80%V_{DRM}		80%V_{DRM}		80%V_{DRM}		V
Rise of on-state current di/dt	50	50	-	-	-	-	A/µs
Case temperature	90	60	90	60	90	60	°C
Equivalent values for RC circuit	22Ω / 0.15µF		22Ω / 0.15µF		22Ω / 0.15µF		

On-state Conduction

Parameter		IRK.F82..	Units	Conditions		
$I_{T(AV)}$	Maximum average on-state current	81	A	180° conduction, half sine wave		
	@ Case temperature	90	°C			
$I_{T(RMS)}$	Maximum RMS current	180	A	T_C = 90°C, as AC switch		
I_{TSM}	Maximum peak, one-cycle, non-repetitive surge current	2200	A	t = 10ms	No voltage reapplied	Sinusoidal half wave, Initial T_J = 125°C
		2300		t = 8.3ms		
		1850		t = 10ms	100% V_{RRM} reapplied	
		1950		t = 8.3ms		
I^2t	Maximum I^2t for fusing	24.2	KA^2s	t = 10ms	No voltage reapplied	
		22.1		t = 8.3ms		
		17.1		t = 10ms	100% V_{RRM} reapplied	
		15.6		t = 8.3ms		
$I^2\sqrt{t}$	Maximum $I^2\sqrt{t}$ for fusing	242	$KA^2\sqrt{s}$	t = 0 to 10ms, no voltage reapplied		
$V_{T(TO)1}$	Low level value of threshold voltage	1.20	V	(16.7% x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), T_J = T_J max.		
$V_{T(TO)2}$	High level value of threshold voltage	1.24		(I > π x $I_{T(AV)}$), T_J = T_J max.		
r_{t1}	Low level value of on-state slope resistance	2.18	mW	(16.7% x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), T_J = T_J max.		
r_{t2}	High level value of on-state slope resistance	2.00		(I > π x $I_{T(AV)}$), T_J = T_J max.		
V_{TM}	Maximum on-state voltage drop	1.96	V	I_{pk} = 350A, T_J = T_J max., t_p = 10ms sine pulse		
I_H	Maximum holding current	600	mA	T_J = 25°C, I_T > 30 A		
I_L	Typical latching current	1000	mA	T_J = 25°C, V_A = 12V, Ra = 6Ω, Ig = 1A		

Switching

	Parameter	IRK.F82..		Units	Conditions
di/dt	Maximum non-repetitive rate of rise	800		A/µs	Gate drive 20V, 20Ω, tr ≤ 1ms, V_D= 80% V_{DRM} T_J = 25°C
t_{rr}	Maximum recovery time	2		µs	I_{TM} = 350A, di/dt = -25A/µs, V_R = 50V, T_J = 25°C
t_q	Maximum turn-off time	N	L		I_{TM} = 350A, T_J = 125°C, di/dt = -25A/µs, V_R = 50V, dv/dt = 400V/µs linear to 80% V_{DRM}
		10	15	µs	

Blocking

	Parameter	IRK.F82..	Units	Conditions
dv/dt	Maximum critical rate of rise of off-state voltage	1000	V/µs	T_J = 125°C., exponential to = 67% V_{DRM}
V_{INS}	RMS isolation voltage	3000	V	50 Hz, circuit to base, T_J = 25°C, t = 1 s
I_{RRM} I_{DRM}	Maximum peak reverse and off-state leakage current	30	mA	T_J = 125°C, rated V_{DRM}/V_{RRM} applied

Triggering

	Parameter	IRK.F82..	Units	Conditions
P_{GM}	Maximum peak gate power	40	W	f = 50 Hz, d% = 50
$P_{G(AV)}$	Maximum peak average gate power	2	W	T_J = 125°C, f = 50Hz, d% = 50
I_{GM}	Maximum peak positive gate current	5	A	T_J = 125°C, $t_p \leq$ 5ms
- V_{GM}	Maximum peak negative gate voltage	5	V	
I_{GT}	Max. DC gate current required to trigger	200	mA	T_J = 25°C, V_{ak} 12V, Ra = 6
V_{GT}	DC gate voltage required to trigger	3	V	
I_{GD}	DC gate current not to trigger	20	mA	T_J = 125°C, rated V_{DRM} applied
V_{GD}	DC gate voltage not to trigger	0.25	V	

Thermal and Mechanical Specifications

	Parameter		IRK.F82..	Units	Conditions
T_J	Max. junction operating temperature range		- 40 to 125	°C	
T_{stg}	Max. storage temperature range		- 40 to 150		
R_{thJC}	Max. thermal resistance, junction to case		0.25	K/W	Per junction, DC operation
R_{thC-hs}	Max. thermal resistance, case to heatsink		0.035	K/W	Mounting surface flat and greased Per module
T	Mounting torque ± 10%	IAP to heatsink	4 - 6 (35 - 53)	Nm	A mounting compound is recommended. The torque should be rechecked after a period of 3 hours to allow for the spread of the compound. Use of cable lugs is not recommendd, busbars should be used and restrained during tightening. Threads must be lubricated with a compound
		busbar to IAP	4 - 6 (35 - 53)	(lb*in)	
wt	Approximate weight		500 (17.8)	g (oz)	

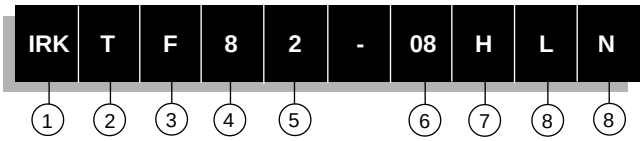
ΔR_{thJC} Conduction

(The following table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction	Rectangular conduction	Units	Conditions
180°	0.016	0.011	K/W	T_J = 125°C
120°	0.019	0.020		
90°	0.024	0.026		
60°	0.035	0.037		
30°	0.060	0.060		

Ordering Information Table

Device Code



1 - Module type

2 - Circuit configuration

3 - Fast SCR

4 - Current rating: $I_{T(AV)}$ x 10 rounded

5 - 1 = option with spacers and longer terminal screws
2 = option with standard terminal screws

6 - Voltage code: Code x 100 = V_{RRM} (See Voltage Ratings Table)

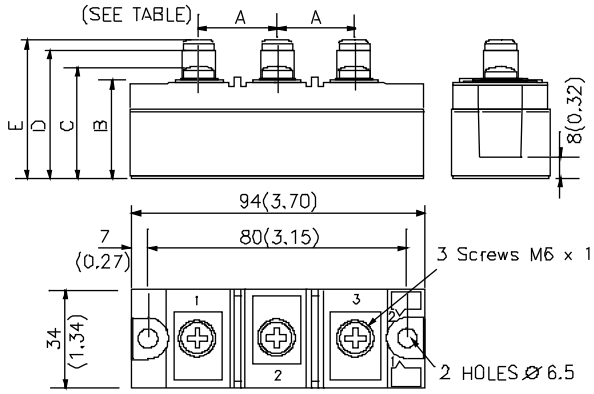
7 - dv/dt code: H ≤ 400V/µs

8 - t_q code: N ≤ 10µs
L ≤ 15µs

9 - None = Standard devices
N = Aluminum nitrade substrate

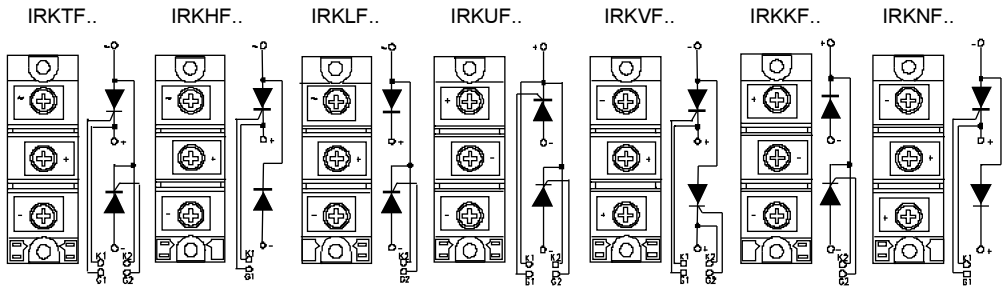
NOTE: To order the Optional Hardware see Bulletin I27900

Outline Table



- All dimensions in millimeters (inches)
- Dimensions are nominal
- Full engineering drawings are available on request
- UL identification number for gate and cathode wire: UL 1385
- UL identification number for package: UL 94V0

For all types	A	B	C	D	E
IRK...1	25 (0.98)	----	----	41 (1.61)	47 (1.85)
IRK...2	23 (0.91)	30 (1.18)	36 (1.42)	----	----



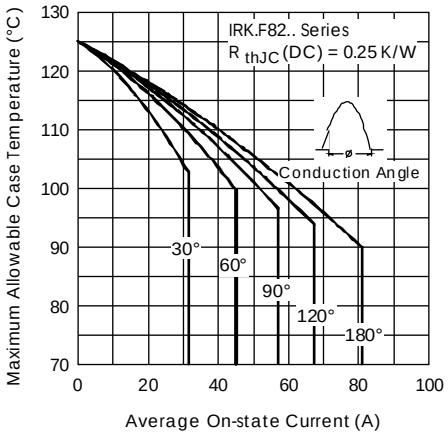


Fig. 1 - Current Ratings Characteristics

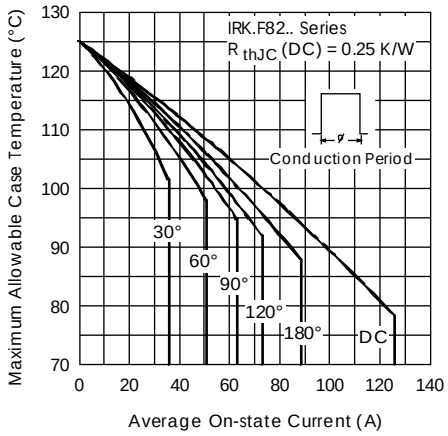


Fig. 2 - Current Ratings Characteristics

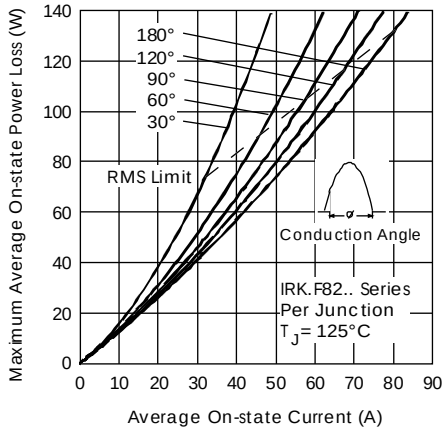


Fig. 3 - On-state Power Loss Characteristics

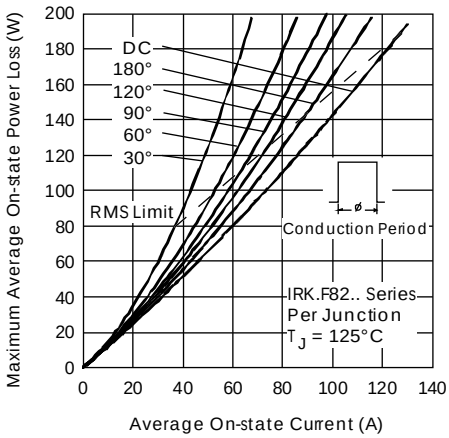


Fig. 4 - On-state Power Loss Characteristics

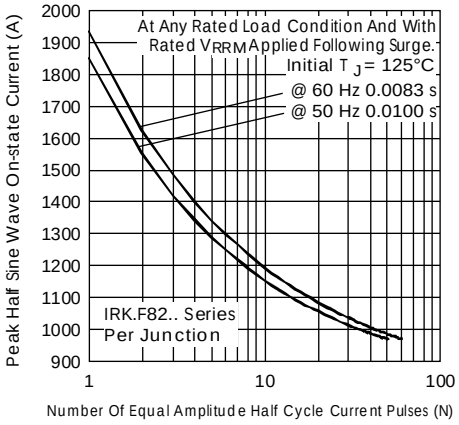

Peak Half Sine Wave On-state Current (A)
Number Of Equal Amplitude Half Cycle Current Pulses (N)
At Any Rated Load Condition And With
Rated VRRM Applied Following Surge.
Initial T J= 125°C
@ 60 Hz 0.0083 s
@ 50 Hz 0.0100 s
IRK.F82.. Series
Per Junction

Fig. 5 - Maximum Non-Repetitive Surge Current

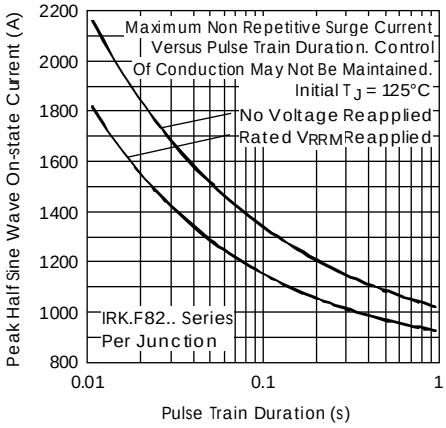

Peak Half Sine Wave On-state Current (A)
Pulse Train Duration (s)
Maximum Non Repetitive Surge Current
Versus Pulse Train Duration. Control
Of Conduction May Not Be Maintained.
Initial T J = 125°C
No Voltage Reapplied
Rated VRRM Reapplied
IRK.F82.. Series
Per Junction

Fig. 6 - Maximum Non-Repetitive Surge Current

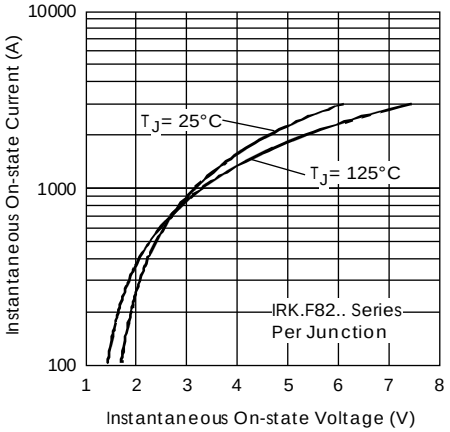


Fig. 7 - On-state Voltage Drop Characteristics

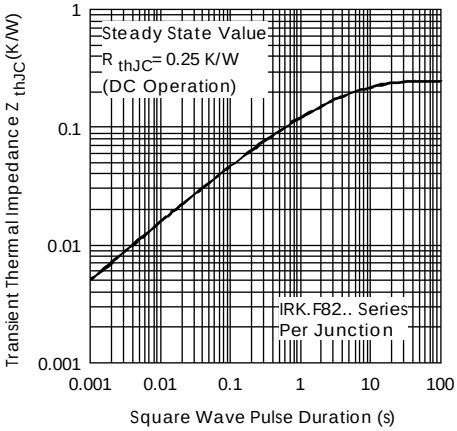


Fig. 8 - Thermal Impedance Z_{thJC} Characteristic

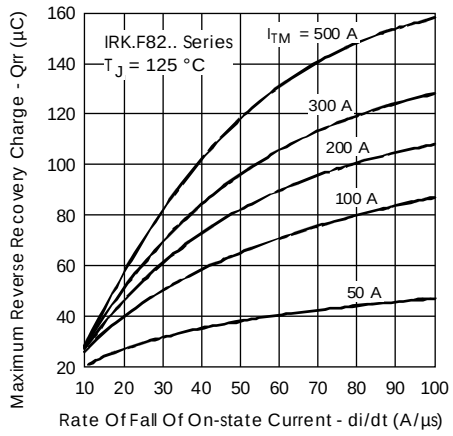

IRK.F82.. Series
T J = 125 °C
I TM = 500 A
300 A
200 A
100 A
50 A
Maximum Reverse Recovery Charge - Qrr (µC)
Rate Of Fall Of On-state Current - di/dt (A/µs)

Fig. 9 - Reverse Recovery Charge Characteristic

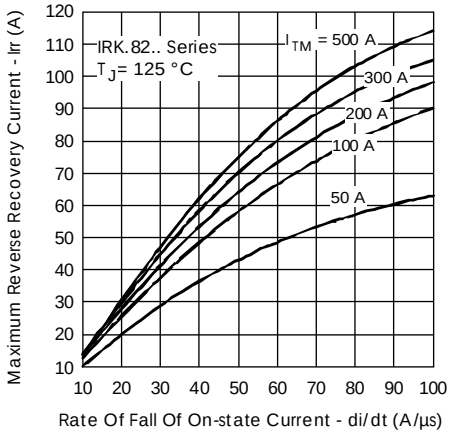


Fig. 10 - Reverse Recovery Current Characteristic

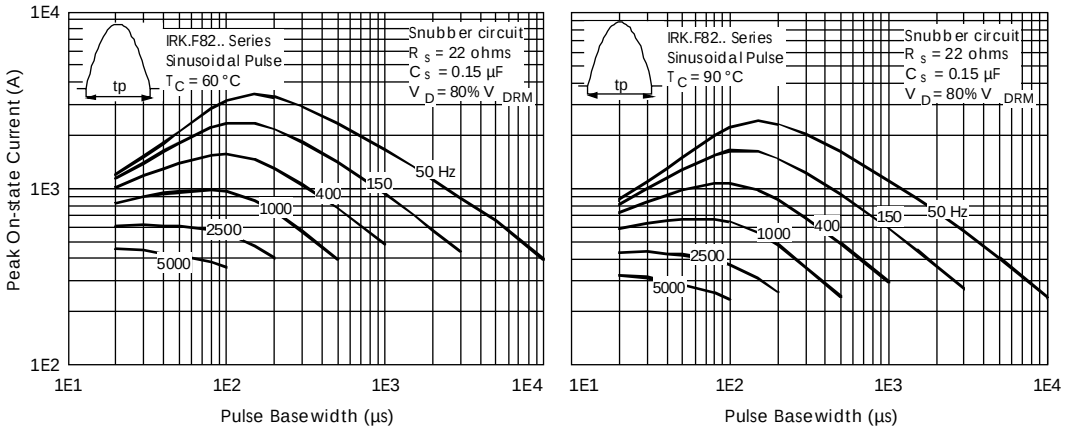


Fig. 11 - Frequency Characteristics

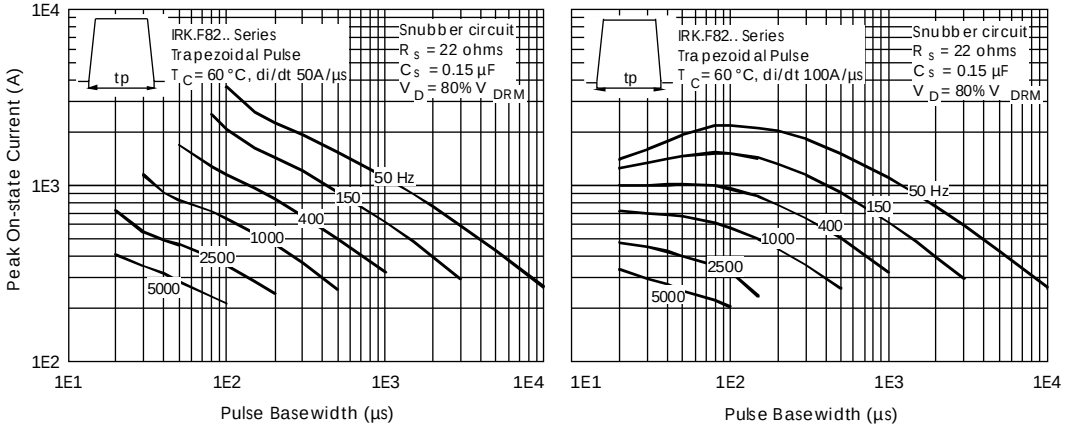


Fig. 12 - Frequency Characteristics

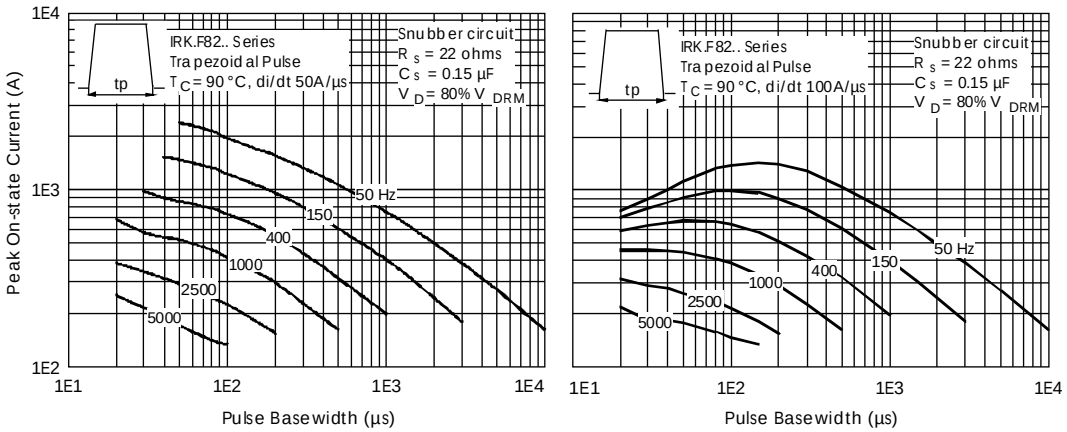


Fig. 13 - Frequency Characteristics

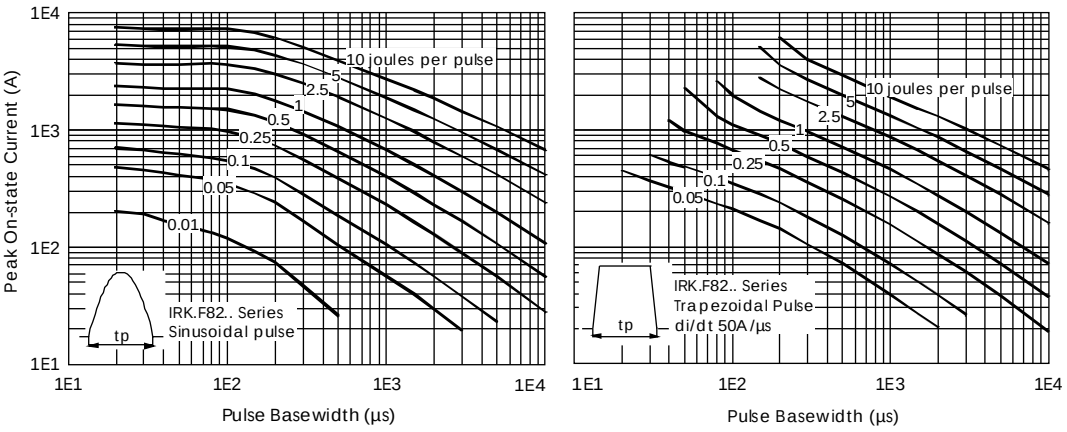


Fig. 14 - Maximum On-state Energy Power Loss Characteristics

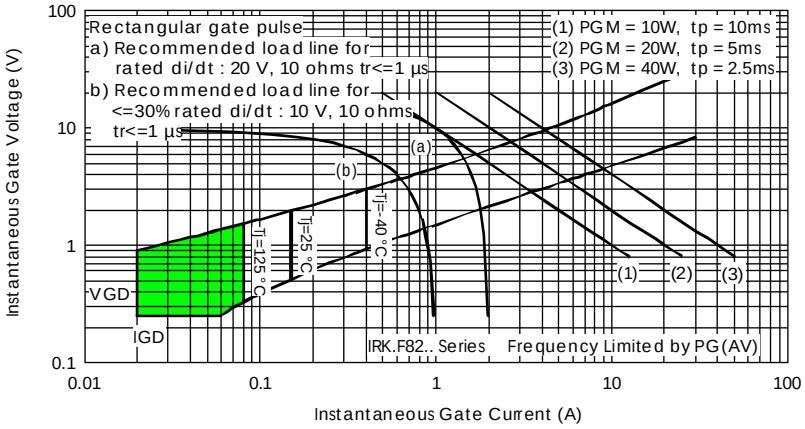


Fig. 15 - Gate Characteristics